



General Features

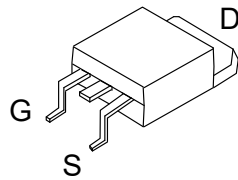
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

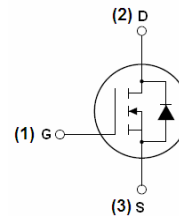
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

Product Summary

BVDSS	60	V
RDS(on),Typ.@ VGS=10 V	23	mΩ
ID	30	A



TO-252



Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Symbol	Parameter	Max.	Units	
V _{DSS}	Drain-Source Voltage	60	V	
V _{GSS}	Gate-Source Voltage	±20	V	
I _D	Continuous Drain Current	T _C = 25°C	30	A
		T _C = 100°C	20	A
I _{DM}	Pulsed Drain Current ^{note1}	120	A	
EAS	Single Pulsed Avalanche Energy ^{note2}	72	mJ	
P _D	Power Dissipation	T _C = 25°C	55	W
R _{θJC}	Thermal Resistance, Junction to Case	2.7	°C/W	
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +175	°C	

**Electrical Characteristics** ($T_J=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=48V, V_{GS}=0V,$	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.6	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note3</small>	$V_{GS}=10V, I_D=15A$	-	23	36	m Ω
		$V_{GS}=4.5V, I_D=10A$	-	29	42	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V,$ $f=1.0MHz$	-	1562	-	pF
C_{oss}	Output Capacitance		-	75.4	-	pF
C_{rss}	Reverse Transfer Capacitance		-	66.8	-	pF
Q_g	Total Gate Charge	$V_{DS}=30V, I_D=15A,$ $V_{GS}=10V$	-	25	-	nC
Q_{gs}	Gate-Source Charge		-	4.5	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	6.5	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=30V, I_D=15A,$ $R_G=1.8\Omega, V_{GS}=10V$	-	7.5	-	ns
t_r	Turn-on Rise Time		-	21	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	16	-	ns
t_f	Turn-off Fall Time		-	23.5	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	30	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	120	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=30A$	-	-	1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F=15A, di/dt=100A/\mu s$	-	29	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	45	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : $T_J=25^\circ\text{C}, V_{DD}=30V, V_G=10V, L=0.5mH, R_g=25\Omega$ 3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$



Test Circuit

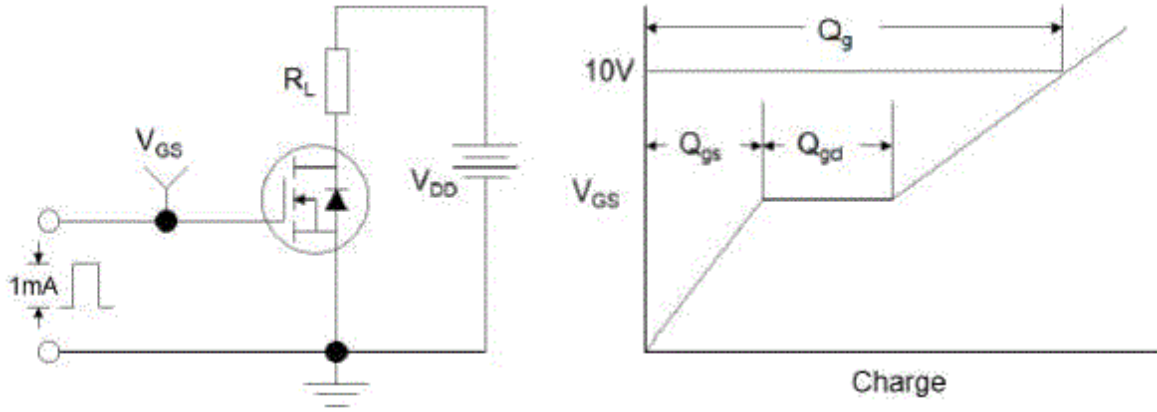


Figure1:Gate Charge Test Circuit & Waveform

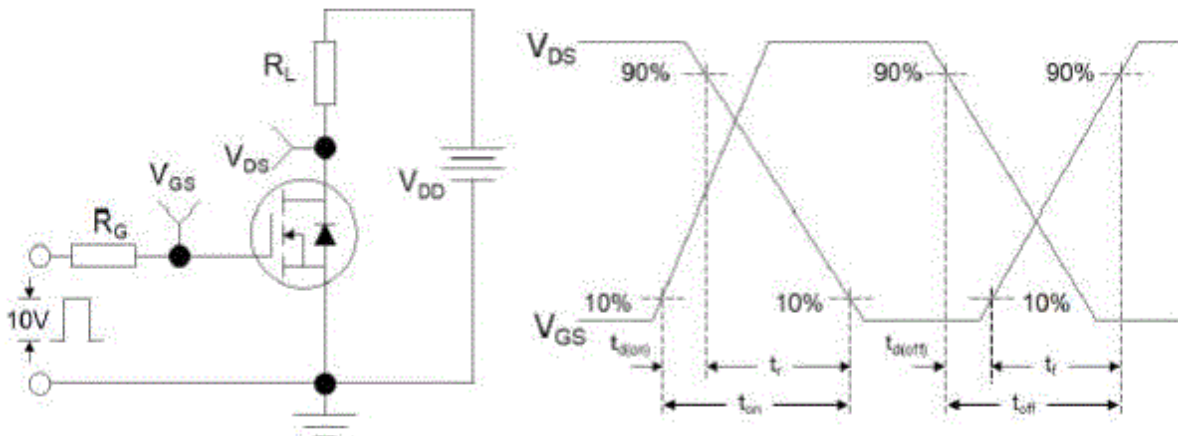


Figure 2: Resistive Switching Test Circuit & Waveforms

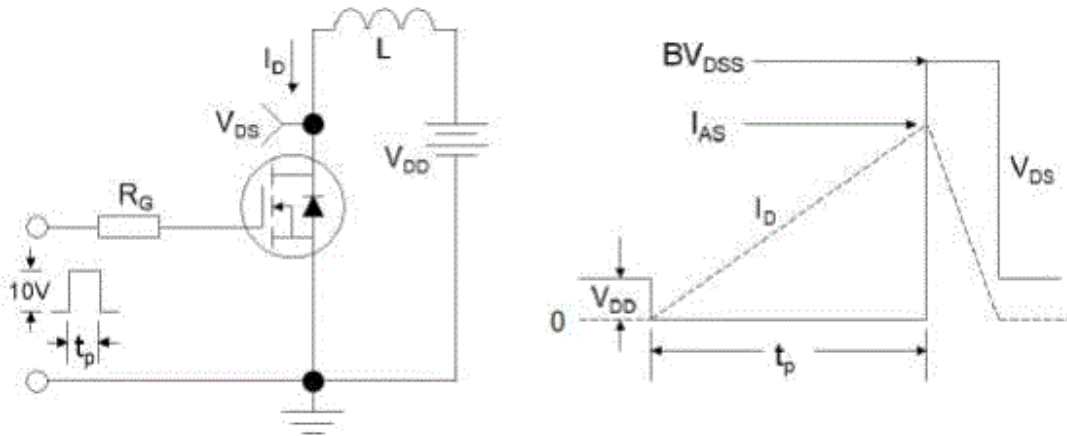


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

Typical Electrical and Thermal Characteristics (Curves)

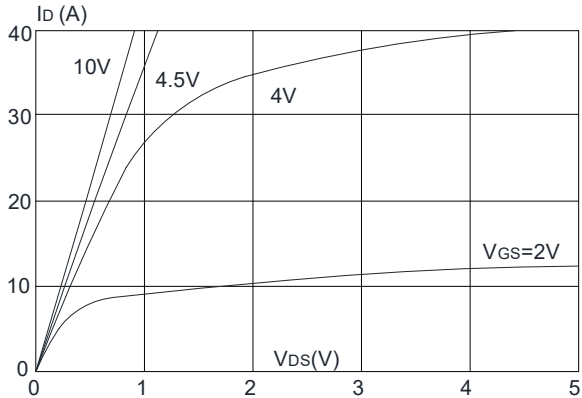


Figure 1: Output Characteristics

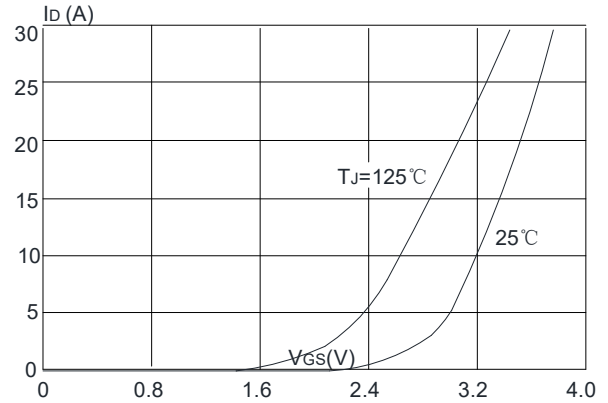


Figure 2: Typical Transfer Characteristics

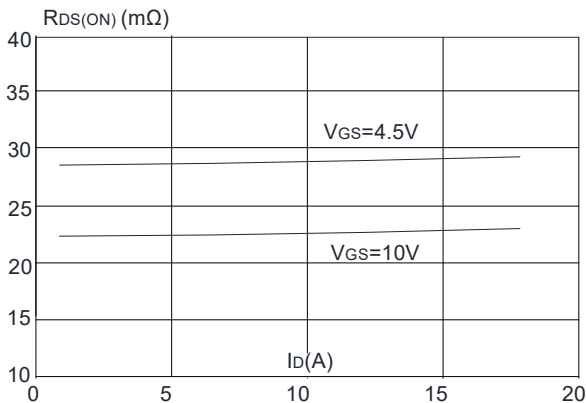


Figure 3: On-resistance vs. Drain Current

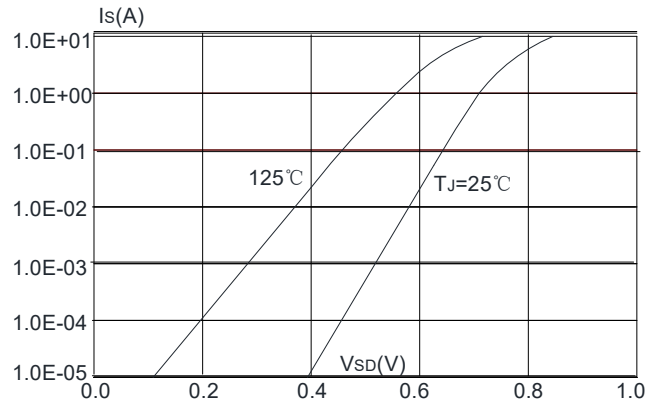


Figure 4: Body Diode Characteristics

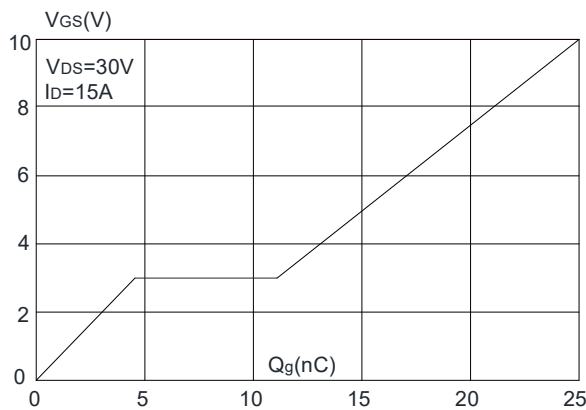


Figure 5: Gate Charge Characteristics

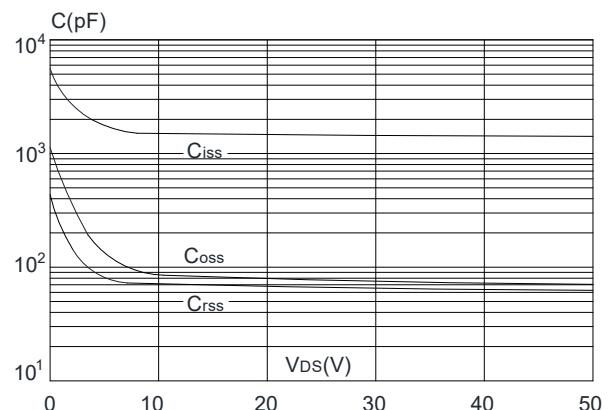


Figure 6: Capacitance Characteristics

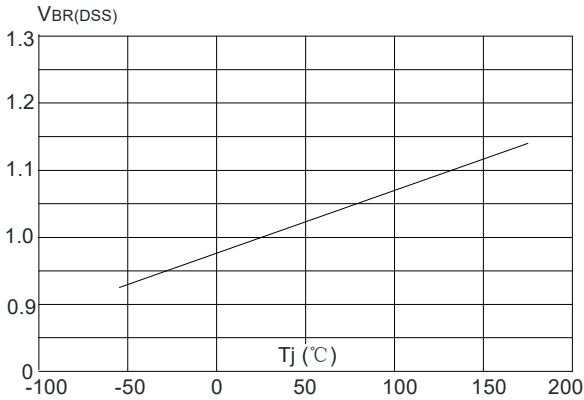


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

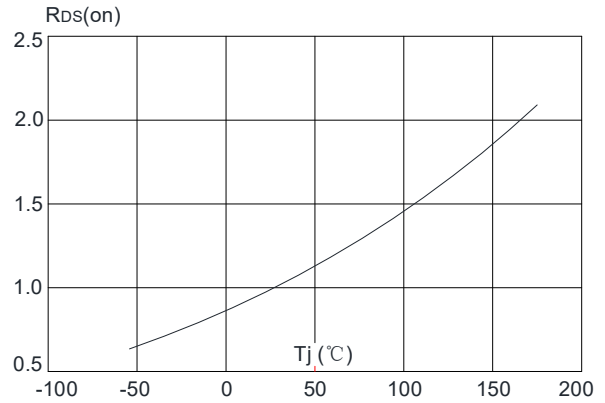


Figure 8: Normalized on Resistance vs. Junction Temperature

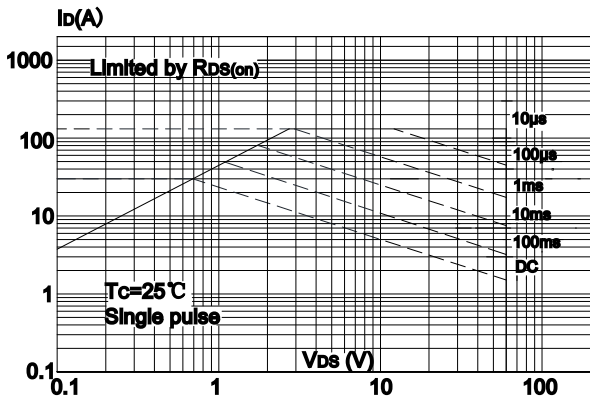


Figure 9: Maximum Safe Operating Area

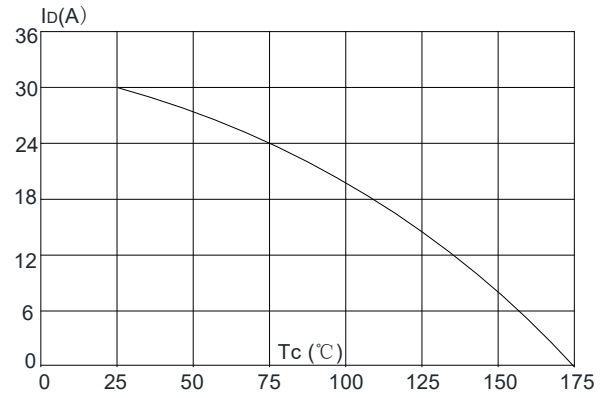


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

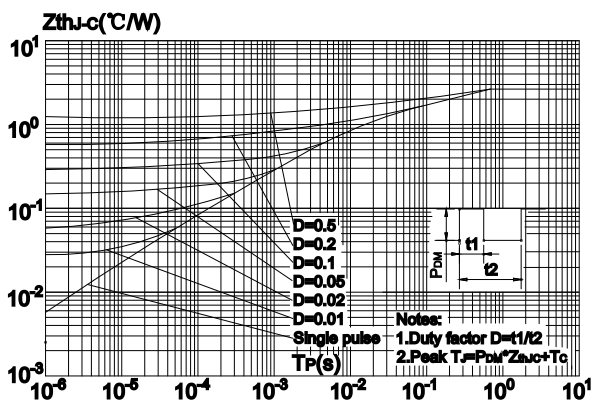
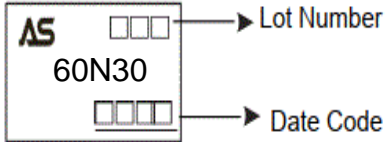
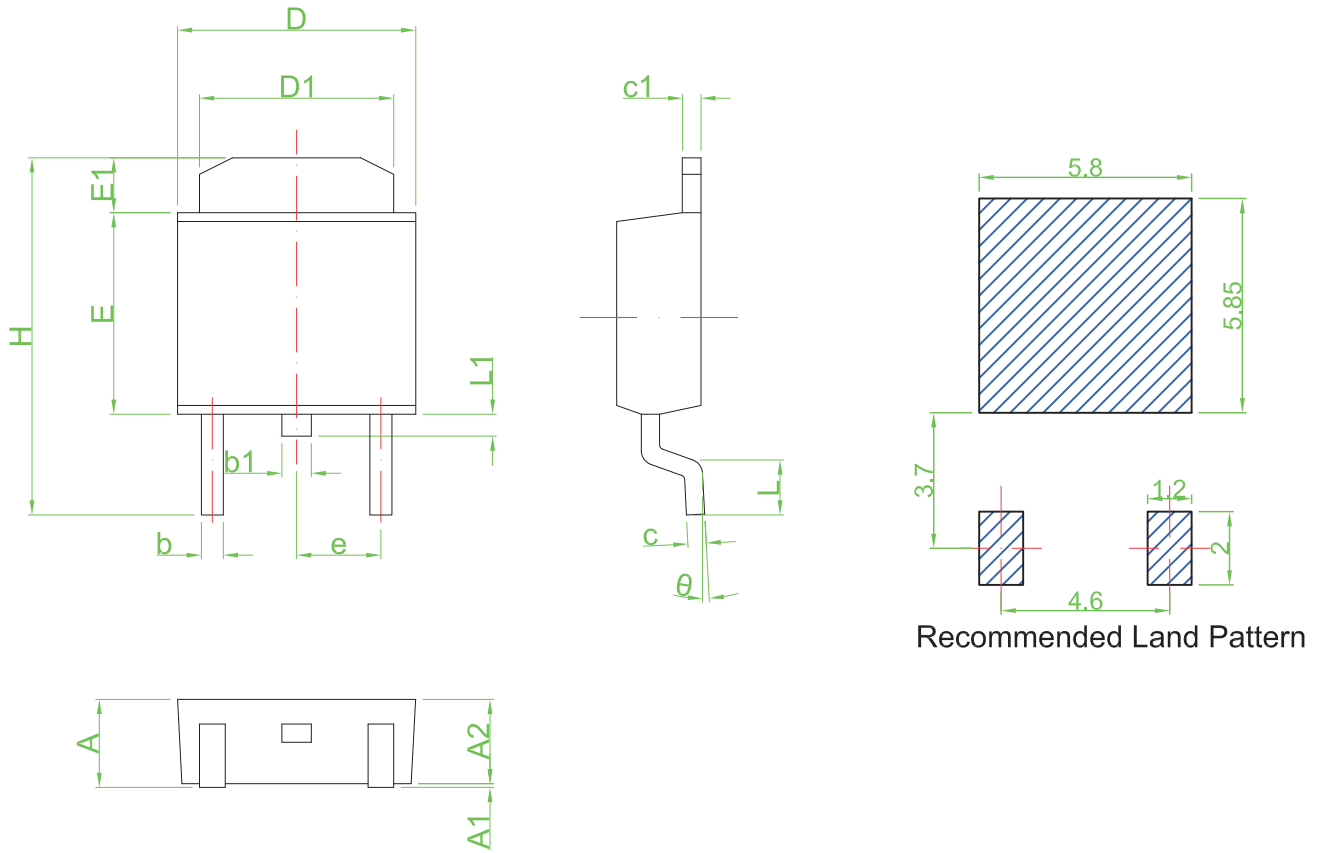


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

Ordering and Marking Information

Ordering Device No.	Marking	Package	Packing	Quantity
ASDM60N30KQ-R	60N30	TO-252	Tape&Reel	2500/Reel

PACKAGE	MARKING
TO-252	 <p>AS □□□ → Lot Number 60N30 □□□□ → Date Code</p>



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	2.25	2.65	0.089	0.104
A1	0.00	0.15	0.000	0.006
A2	2.20	2.40	0.087	0.094
b	0.50	0.70	0.020	0.028
b1	0.70	0.90	0.028	0.035
c	0.46	0.66	0.018	0.026
c1	0.46	0.66	0.018	0.026
D	6.30	6.70	0.248	0.264
D1	5.20	5.40	0.205	0.213
E	5.30	5.70	0.209	0.224
E1	1.40	1.60	0.055	0.063
H	9.40	9.90	0.370	0.390
e	2.30 TYP		0.09 TYP	
L	1.40	1.77	0.055	0.070
L1	0.50	0.70	0.020	0.028
θ	0°	8°	0°	8°

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